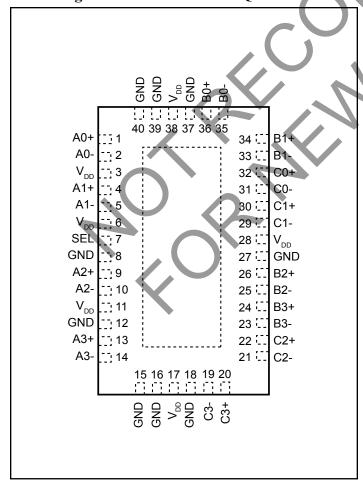


3.3V, PCI Express® 3.0 2-Lane, 2:1 Mux/DeMux Switch, with Single Enable

### **Features**

- 4 Differential Channel, 2:1 Mux/DeMux
- PCI Express® 3.0 Performance, 8.0Gbps
- Bi-directional Operation
- Low Bit-to-Bit Skew, 10ps max
- Low channel-to-channel skew, 20ps max
- Low Crosstalk: -35dB@4 GHz
- High Off Isolation: -22dB@4 GHz (8.0Gbps)
- Low insertion loss: -1.3dB@4 GHz (8.0Gbps)
- Return loss: -21dB@4 GHz
- Support for DP1.2 HBR2, HBR, RBR
- Supply Voltage 3.3V
- Industrial Temperature Range: -40°C to 85°C
- Packaging (Pb-free & Green):
  - 42-contact, TQFN (ZH42), 3.5 x 9mm
  - 40-contact, TQFN (ZL40), 3 x 6mm

# Pin Configuration - 40- Contact TQFN



### **Description**

The PI3PCIE3412 is an 8 to 4 differential channel multiplexer/ demultiplexer switch. This solution can switch 2 full PCI Express® 3.0, lanes to one of two locations. Using a unique design technique, Diodes has been able to minimize the impedance of the switch such that the attenuation observed through the switch is minimal. The unique design technique also offers a layout targeted for PCI Express signals, which minimizes the channel to channel skew as well as channel to channel crosstalk as required by the PCI Express specification. PI3PCIE3412 can also be used for application up to 12Gbps

# Application

1

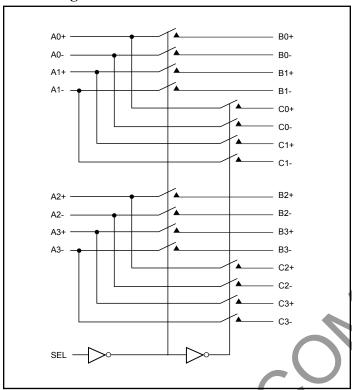
Routing of PCI Express 3.0, DP1.2, USB3.0, SAS2.0, SATA3.0, XAUI, RXAUI signals with low signal attenuation.

Pin Configuration - 42- Contact TQFN					
	>	GND GND GND			
		3 IB IB IB			
GND	42	2 41 40 39	38 🗔	R∩±	
A0+		:	37		
	3		36		
GND		;	35		
	<u> </u>	;	34		
A1+			33		
	<u>:</u> 7		32		
V <sub>DD</sub>	; 8		31		
SEL			30		
	<u></u> ; 10		29		
A2+	<u> </u>		28	B2-	
A2-	12		27	B3+	
V <sub>DD</sub>	<u> </u>		26	B3-	
GND	<u></u> : 14		25	C2+	
A3+	<u> </u>	:	24	C2-	
A3-	<u></u> : 16	;	23	C3+	
	17	زـــــــــــــــــــــــــــــــــــــ	22	C3-	
	[ - ·	8 19 20 21			
		1000			
	O O O O				





# **Block Diagram**



# **Truth Table**

Function	SEL
A <sub>N</sub> to B <sub>N</sub>	L
A <sub>N</sub> to C <sub>N</sub>	H





# **Pin Description**

Pin #				
42-TQFN	40-TQFN	Pin Name	I/O	Description
2	1	A0+	1.00	o: IVO OL LO D. (A
3	2	A0-	I/O	Signal I/O, Channel 0, Port A
6	4	A1+	I/O	Circulation Character Dept.
7	5	A1-	I/O	Signal I/O, Channel 1, Port A
11	9	A2+	I/O	Circult/O Channel 2 Post 4
12	10	A2-	I/O	Signal I/O, Channel 2, Port A
15	13	A3+	I/O	Signal I/O, Channel 3, Port A
16	14	A3-	1/0	Signal 1/O, Chamners, Port A
38	36	B0+	I/O	Simulation Change to Death
37	35	В0-	I/O	Signal I/O, Channel 0, Port B
36	34	B1+	I/O	Signal I/O, Channel 1, Port B
35	33	B1-	1/0	Signal VO, Channel 1, Port B
29	26	B2+	I/O	Signal I/O, Channel 2, Port B
28	25	B2-	1/0	Signary O, Channel 2, Fort B
27	24	B3+	I/O	Signal I/O, Channel 3, Port B
26	23	В3-	1/0	Signal 1/0, Channel 5, Fort B
34	32	C0+	I/O	Signal I/O, Channel 0, Port C
33	31	C0-	1/0	Signal 1/0, Chairner 0, Fort C
32	30	C1+	I/O	Signal I/O, Channel 1, Port C
31	29	C1-	110	Signal 170, Chamier 1, 1 of t C
25	22	C2+	I/O	Signal I/O, Channel 2, Port C
24	21	C2-	1/0	Signal 170, Chamie 2, Fort C
23	20	C3+	I/O	Signal I/O, Channel 3, Port C
22	19	C3-	1,0	orginal 1705, Chammer 3, 1 Of C
9	7	SEL	I	Operation mode Select (when SEL=0: A→B, when SEL=1: A→C
5, 8, 13,18, 20, 30, 40, 42	3, 6, 11, 17, 28, 38	$V_{ m DD}$	Pwr	3.3V ±10% Positive Supply Voltage
1, 4, 10, 14, 17, 19, 21, 39, 41, Center Pad	8, 12, 15, 16, 18, 27, 37, 39, 40	GND	Pwr	Power ground



### **Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)

<u> </u>	
Storage Temperature	65°C to +150°C
Supply Voltage to Ground Potential	0.5V to +4.6V
Channel DC Input Voltage	0.5V to 1.5V
DC Output Current	120mA
Power Dissipation	0.5W
SEL DC Input Voltage	0.5V to 4.6V

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### **Electrical Characteristics**

**Recommended Operating Conditions** 

Symbol	Parameter	Conditions Min. Typ.	Max.	Units
$V_{\mathrm{DD}}$	3.3V Power Supply	3.0 3.3	3.6	V
I <sub>DD</sub>	Total current from V <sub>DD</sub> 3.3V supply	$SEL = 0V \text{ or } V_{DD} $ 0.15	1	mA
V <sub>I/O</sub> -DIF	Differential Voltage (differential pins)		1.6	V <sub>ppd</sub>
V <sub>I/O-CM</sub>	Common Mode Voltage (differiential pins)	0	0.8	V
T <sub>A</sub>	Operating temperature range	-40	85	°C

# DC Electrical Characteristics for Switching over Operating Range

Parameters	Description	Test Conditions <sup>(I)</sup>	Min.	Typ.(1)	Max.	Units
V <sub>IH</sub> - SEL	Input HIGH Voltage, SEL Input		2		3.6	
V <sub>IL</sub> - SEL	Input LOW Voltage, SEL Input		0		0.8	V
$V_{IK}$	Clamp Diode Voltage	$V_{DD} = Max.$ , $I_{IN} = -18mA$		-0.7	-1.2	
IIH	Input HIGH Current, SEL	$V_{DD} = Max., V_{IN} = V_{DD}$			±5	
$I_{IL}$	Input LOW Current, SEL	$V_{\mathrm{DD}} = \mathrm{Max.},  V_{\mathrm{IN}} = 0 \mathrm{V}$			±5	μΑ
I <sub>IN</sub> - SEL	Input Leakage Current, SEL Input	$V_{IN} = V_{IH}$ - SEL Max or $V_{IL}$ - SEL Min	-10		+10	μΑ
IIH	Input HIGH Current, A <sub>X</sub> , B <sub>X</sub> , C <sub>X</sub>	$V_{\mathrm{DD}} = \mathrm{Max.},  V_{\mathrm{IN}} = 1.5 \mathrm{V}$	-10		+10	
$I_{IL}$	Input LOW Current, $A_X$ , $B_X$ , $C_X$	$V_{DD} = Max., V_{IN} = 0V$	-10		+10	μΑ
IOZH	High Z HIGH Current, $B_X$ , $C_{\overline{X}}$	$V_{DD} = Max., V_{IN} = 1.5V$	-10		+10	μΑ
IOZL	HighZ LOW Current, BX, CX	$V_{DD} = Max., V_{IN} = 0V$	-10		+10	μΑ
C <sub>I/O</sub> -ON	ON state I/O capacitance			1.5		pF
RON	ON state resistance	$V_{\rm DD} = 3.3 \text{V}, \text{IO} = 8 \text{mA}, V_{\rm IN} = 0.8 \text{V}$		5		Ω

Note:

### **Switching Characteristics**

Parameters	Description	<b>Test Conditions</b>	Min.	Тур.	Max.	Units
tpZH, tpZL	Line Enable Time - SEL to $A_N$ , $B_N$ , $C_N$		2	20	25	no
tpHZ, tPLZ	Line Disable Time - SEL to A <sub>N</sub> , B <sub>N</sub> , C <sub>N</sub>		0.5	5	25	ns
t <sub>b-b</sub>	Bit-to-bit skew within the same differential pair			5	10	ps
t <sub>ch-ch</sub>	Channel-to-channel skew				20	ps

Typical values are at  $V_{DD} = 3.3V$ ,  $T_A = 25$ °C ambient and maximum loading.

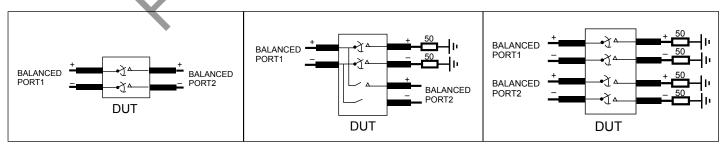


# **Dynamic Electrical Characteristics**

Parameter	Description	<b>Test Conditions</b>	Min.	Typ. <sup>(1)</sup>	Max.	Units
		f= 50MHz - 1.25GHz		-0.8	-1	
DDIL	Differential Insertion Loss	f=1.25GHz - 2.5GHz		-1.0	-1.2	dB
DDIL	$(V_{IN} = -10 dBm, DC = 0V)$	f=2.5GHz - 4GHz		-1.3	-1.6	иь
		f=5GHz		-1.8	-2.2	
		f= 50MHz - 1.25GHz	-26.3	-32.9		
DDII	Differential Off Isolation	f=1.25GHz - 2.5GHz	-21.4	-26.7		JD.
DDIL <sub>OFF</sub>	Differential Off Isolation	f=2.5GHz - 4GHz	-17.6	-22		dB
		f=5GHz	-16	-20		
		f= 50MHz - 1.25GHz	-20	-25		
DDDI	DDRL Differential Return Loss	f=1.25GHz - 2.5GHz	-18.4	-23		dB
DDKL		f=2.5GHz - 4GHz	-16.8	-21		ив
		f=5GHz	-9.6	-12		
		f= 50MHz - 1.25GHz	-34.1	-42.6		
DDNEXT	Near End Crosstalk	f=1.25GHz - 2.5GHz	-30.5	-38.1		dB
DDNEXI	Iveal Eliu Glosstalk	f=2.5GHz - 4GHz	-28.1	-35.1		шь
		f=5GHz	-27.2	-34		
		Insertion loss 1.5dB, V <sub>IN</sub> =0.623Vpp, DC=0V		4.0		
		Insertion loss 1.5dB, V <sub>IN</sub> =0.623Vpp, DC=0.9V		4.0		
V <sub>I F</sub> Max Signal Frequency Range	Max Signal Frequency Range	Insertion loss 3dB, V <sub>IN</sub> =0.623Vpp, DC=0V		8.0		GHz
	Insertion loss 3dB, V <sub>IN</sub> =0.623Vpp, DC=0.9V		8.0			
BW	-3dB Bandwidth			8.2		GHz

#### **Notes:**

<sup>1.</sup> Guaranteed by design. Typical values are at  $V_{DD}$  = 3.3V ,  $T_A$  = 25°C ambient and maximum loading.

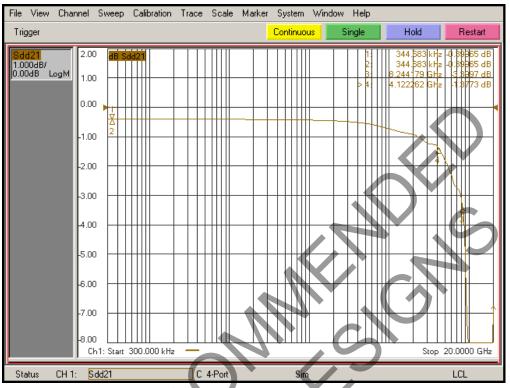


Diff. Insertion Loss and Return Test Circuit

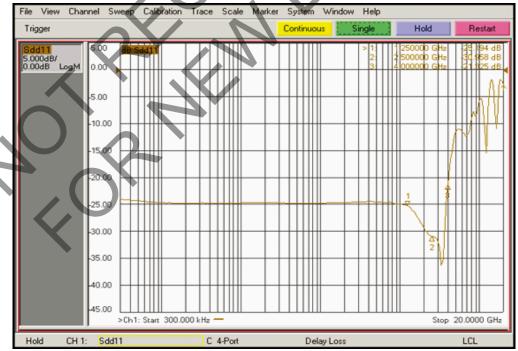
**Diff. Off Isolation Test Circuit** 

Diff. Near End Xtalk Test Circuit



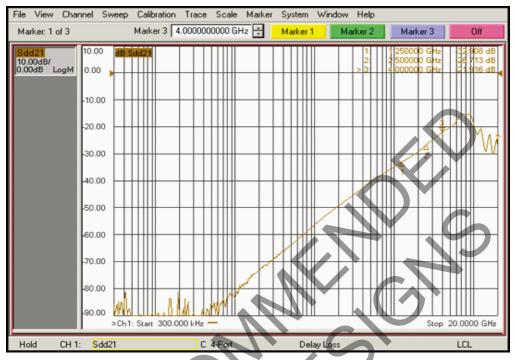


**Differential Insertion Loss** 

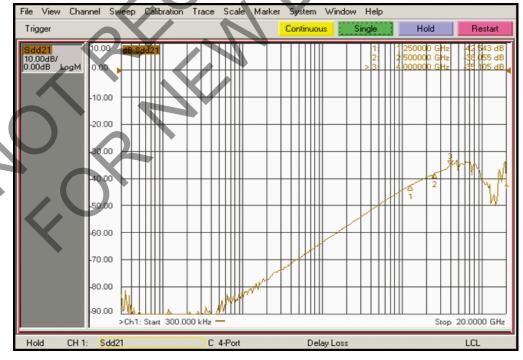


**Differential Return Loss** 



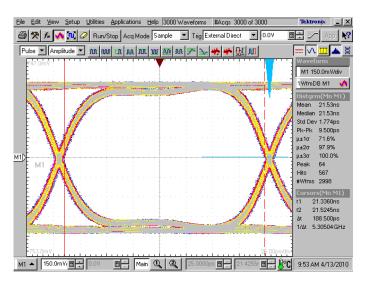


**Differential Off Isolation** 

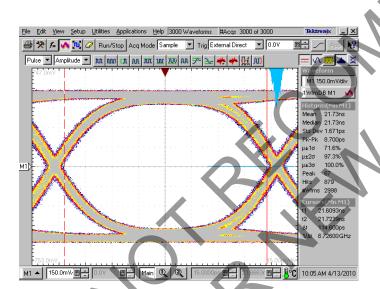


**Differential Crosstalk** 

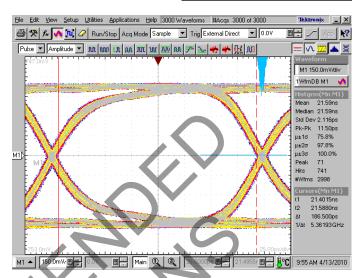




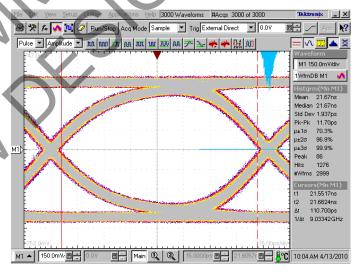
5.0 Gbps RX signal eye without PI3PCIE3412



8.0 Gbps RX signal eye without PI3PCIE3412



5.0 Gbps RX signal eye with PI3PCIE3412

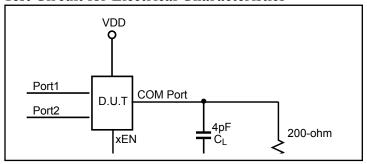


8.0 Gbps RX signal eye with PI3PCIE3412





# **Test Circuit for Electrical Characteristics**<sup>(1-5)</sup>



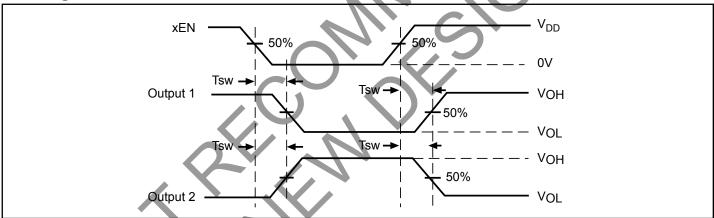
### **Switch Positions**

Test	Switch
t <sub>PLZ</sub> , t <sub>PZL</sub>	3.0V
t <sub>PHZ</sub> , t <sub>PZH</sub>	GND
Prop Delay	Open

#### **Notes:**

- 1. C<sub>L</sub> = Load capacitance: includes jig and probe capacitance.
- 2.  $R_T$  = Termination resistance: should be equal to  $Z_{OUT}$  of the Pulse Generator
- 3. Output 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Output 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. All input impulses are supplied by generators having the following characteristics:  $PRR \le MHz$ ,  $Z_O = 50\Omega$ ,  $t_R \le 2.5$ ns,  $t_F \le 2.5$ ns.
- 5. The outputs are measured one at a time with one transition per measurement.

# **Switching Waveforms**

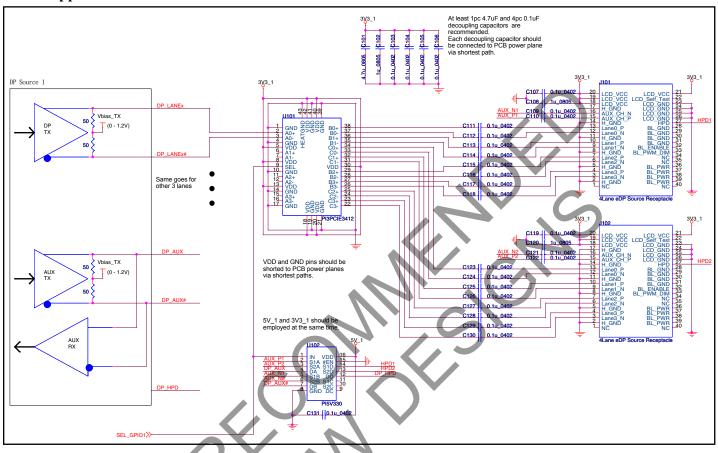


**Voltage Waveforms Enable and Disable Times** 





# **DP1.2** Application



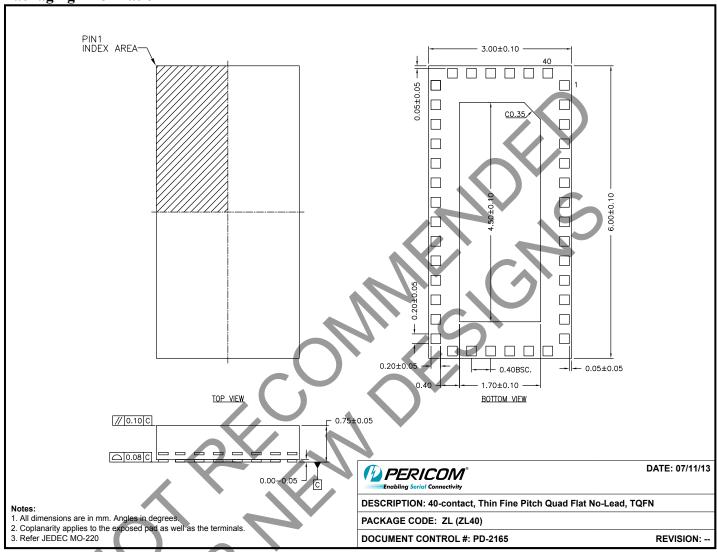
# PART OBSOLETE - USE PI3PCIE3412A





PI3PCIE3412

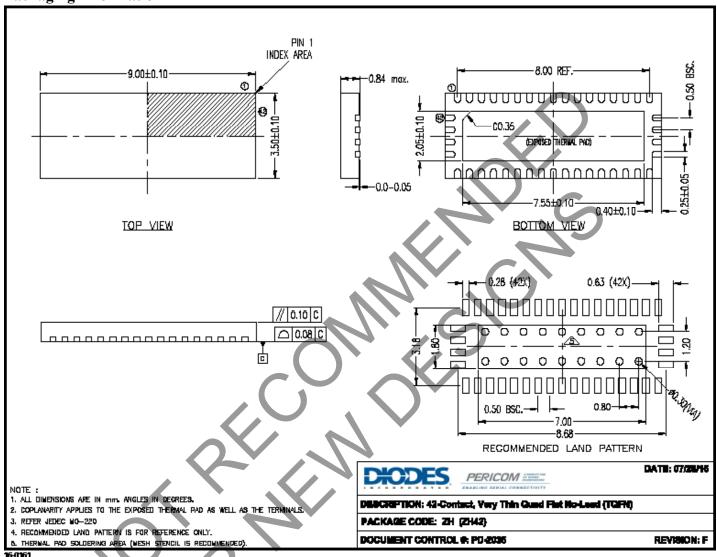
**Packaging Information** 







# **Packaging Information**



Note: For latest package info, please check: http://www.pericom.com/support/packaging/packaging-mechanicals-and-thermal-characteristics/

## **Ordering Information**

Ordering Code	Package Code	Package Description
PI3PCIE3412ZLE	ZL	40-contact, Thin Fine Pitch Quad Flat No-Lead (TQFN)
PI3PCIE3412ZLEX	ZL	40-contact, Thin Fine Pitch Quad Flat No-Lead (TQFN), Tape & Reel
PI3PCIE3412ZHE	ZH	42-contact, Very Thin Quad Flat No-Lead (TQFN)
PI3PCIE3412ZHEX	ZH	42-contact, Very Thin Quad Flat No-Lead (TQFN), Tape & Reel

#### Notes

- · Thermal characteristics can be found on the company web site at www.pericom.com/packaging/
- "E" denotes Pb-free and Green
- · Adding an "X" at the end of the ordering code denotes tape and reel packaging

### PART OBSOLETE - USE PI3PCIE3412A





PI3PCIE3412

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